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DERWENT-ACC- 2002-748537
NO:**DERWENT-WEEK: 200359****COPYRIGHT 2005 DERWENT INFORMATION LTD****TITLE:** Method for manufacturing **capacitor** using atomic layer deposition**INVENTOR: LEE, J W****PATENT-ASSIGNEE: HYNIX SEMICONDUCTOR INC[HYNIN]****PRIORITY-DATA: 2000KR-0076627 (December 14, 2000)****PATENT-FAMILY:**

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 384851 B	May 22, 2003	N/A	000	H01L 027/108
KR 2002046433 A	June 21, 2002	N/A	001	H01L 027/108

APPLICATION-DATA:

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KR 384851B	N/A	2000KR-0076627	December 14, 2000
KR 384851B	Previous Publ.	KR2002046433	N/A
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INT-CL (IPC): H01L027/108**ABSTRACTED-PUB-NO: KR2002046433A****BEST AVAILABLE COPY****BASIC-ABSTRACT:**

NOVELTY - A fabrication method of a capacitor is provided to improve quality and electrical properties by using an ALD(Atomic Layer Deposition) and an ammonia plasma treatment.

DETAILED DESCRIPTION - A lower electrode(21) and a barrier metal(22) are sequentially formed on a semiconductor substrate(20). A TaON dielectric film(23) is then formed on the barrier metal. A TiN upper electrode(24) is formed on the TaON dielectric film(23) by an ALD using $TiCl_4$ as a source gas. The surface of the TaN upper electrode(24) is performed by NH_3 plasma treatment so as to remove Cl radicals.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE CAPACITOR ATOMIC LAYER DEPOSIT

DERWENT-CLASS: L03 U11 U14

CPI-CODES: L03-G04A; L04-C11C2; L04-C12B; L04-C14A;

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